

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Canceled)

2. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode having a first portion and a second portion over the interlayer insulating film, wherein the first portion has a leveling surface;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;

an insulating film over the leveling surface of the anode and an upper surface of the bank;

an organic compound layer over the anode with the insulating film interposed therebetween; and

a cathode over the organic compound layer,

wherein the insulating film is formed from an organic resin film contains at least one of polyamide and acrylic.

3. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode having a first portion and a second portion over the interlayer insulating film, wherein the first portion has a leveling surface;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;  
an insulating film over the leveling surface of the anode and an upper surface of the bank;  
an organic compound layer over the anode with the insulating film interposed therebetween; and  
a cathode over the organic compound layer,  
wherein the insulating film contains at least one of polyamide and acrylic, and  
wherein the insulating film is at a film thickness of 1 to 5nm.

4. (Canceled)

5. (Currently Amended) A light emitting device comprising:  
a thin film transistor on an insulating surface;  
an interlayer insulating film over the thin film transistor;  
an anode having a first portion and a second portion over the interlayer insulating film, wherein the first portion has a leveling surface;  
a wiring electrically connected to the thin film transistor and the anode;  
a bank over the wiring and a portion of the anode;  
an insulating film over the leveling surface of the anode and an upper surface of the bank;  
an organic compound layer over the anode with the insulating film interposed therebetween; and  
a cathode over the organic compound layer,  
wherein the insulating film contains at least one of polyamide and acrylic, and  
wherein the anode is formed from indium tin oxide.

6. (Currently Amended) A light emitting device comprising:  
a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;  
an anode having a first portion and a second portion over the interlayer insulating film, wherein the first portion has a leveling surface;  
a wiring electrically connected to the thin film transistor and the anode;  
a bank over the wiring and a portion of the anode;  
an insulating film over the leveling surface of the anode and an upper surface of the bank;  
an organic compound layer over the anode with the insulating film interposed therebetween; and  
a cathode over the organic compound layer,  
~~wherein the insulating film is formed from an organic resin film contains at least one of polyamide and acrylic,~~  
wherein the insulating film is at a film thickness of 1 to 5nm, and  
wherein the anode is formed from indium tin oxide.

7.-12. (Canceled)

13. (Original) A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

14. (Original) A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

15. (Original) A device according to claim 2, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

16. (Original) A device according to claim 2,

wherein the bank is processed by a plasma; and

wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

17. (Withdrawn) A device according to claim 2,

wherein a second insulating film is formed over the interlayer insulating film; and

wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

18. (Original) A device according to claim 2,

wherein the light emitting device is in combination with an electric device; and

wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

19. (Original) A device according to claim 3, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

20. (Original) A device according to claim 3, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

21. (Original) A device according to claim 3, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

22. (Original) A device according to claim 3,

wherein the bank is processed by a plasma; and

wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

23. (Withdrawn) A device according to claim 3,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

24. (Original) A device according to claim 3,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display,  
a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

25.-30. (Canceled)

31. (Original) A device according to claim 5, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

32. (Original) A device according to claim 5, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

33. (Original) A device according to claim 5, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

34. (Original) A device according to claim 5,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

35. (Withdrawn) A device according to claim 5,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

36. (Original) A device according to claim 5,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

37. (Original) A device according to claim 6, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

38. (Original) A device according to claim 6, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

39. (Original) A device according to claim 6, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

40. (Original) A device according to claim 6,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.
41. (Withdrawn) A device according to claim 6,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.
42. (Original) A device according to claim 6,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.
43. (Canceled)
44. (Previously Presented) A device according to claim 2,  
wherein the bank is formed from a resin insulating film.
45. (Previously Presented) A device according to claim 3,  
wherein the bank is formed from a resin insulating film.
46. (Previously Presented) A device according to claim 5,

wherein the bank is formed from a resin insulating film.

47. (Previously Presented) A device according to claim 6,  
wherein the bank is formed from a resin insulating film.

48. (Canceled)

49. (Previously Presented) A device according to claim 2,  
wherein the leveling surface of the anode is formed by a wiping process using a  
porous material.

50. (Previously Presented) A device according to claim 3,  
wherein the leveling surface of the anode is formed by a wiping process using a  
porous material.

51. (Previously Presented) A device according to claim 5,  
wherein the leveling surface of the anode is formed by a wiping process using a  
porous material.

52. (Previously Presented) A device according to claim 6,  
wherein the leveling surface of the anode is formed by a wiping process using a  
porous material.